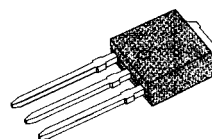


PNP Transistor KSA1241 datasheet

POWER AMPLIFIER APPLICATIONS

- Low Collector Emitter Saturation Voltage
- Complement to KSC3076

I-PACK



ABSOLUTE MAXIMUM RATINGS (Ta=25 °C)

Characteristic	Symbol	Rating	Unit
Collector Base Voltage	V _{CB0}	-55	V
Collector Emitter Voltage	V _{CEO}	-50	V
Emitter Base Voltage	V _{EB0}	-5	V
Base Current	I _B	-1	A
Collector Current	I _C	-2	A
Collector Dissipation (Ta=25 °C)	P _C	1	W
Collector Dissipation (Tc=25 °C)	P _C	10	W
Junctin Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55~150	°C

ELECTRICAL CHARACTERISTICS (Ta=25 °C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Emitter Breakdown Voltage	BV _{CEO}	I _C = -10mA, I _B = 0	-50			V
Collector Cutoff Current	I _{CB0}	V _{CB} = -50V, I _E = 0			-1	μA
Emitter Cutoff Current	I _{EB0}	V _{EB} = -5V, I _C = 0			-1	μA
DC Current Gain	h _{FE1}	V _{CE} = -2V, I _C = -0.5A	70		240	
	h _{FE2}	V _{CE} = -2V, I _C = -1.5V	40			
Collector Emitter Saturation Voltage	V _{CE(sat)}	I _C = -1A, I _B = -0.05A			-0.5	V
Base Emitter Saturation Voltage	V _{BE(sat)}	I _C = -1A, I _B = -0.05A			-1.2	V
Current Gain Bandwidth Product	f _T	V _{CE} = -2V, I _C = -0.5A		100		MHz
Output Capacitance	C _{ob}	V _{CN} = -10V, f = 1MHz		40		pF
Turn On Time	t _{on}	V _{CC} = -30V		0.1		μs
Storage Time	t _{stg}	-I _{B1} = I _{B2} = 0.05A		1		μs
Fall Time	t _f			0.1		μs

h_{FE}(1) CLASSIFICATION

Classification	O	Y
h _{FE1}	70~140	120~240